

Fast Switching Emitter Controlled Diode







Green

Features:

- 600V Emitter Controlled technology
- Fast recovery
- Soft switching
- Low reverse recovery charge
- Low forward voltage
- 175°C junction operating temperature
- Easy paralleling
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models: <u>http://www.infineon.com</u>

Applications:

- Welding
- Motor drives

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PG-TO247-3	nc ^C

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Туре	V _{RRM}	I _F	<i>V</i> _{F,<i>Tj</i>=25℃}	T _{j,max}	Marking	Package
IDW100E60	600V	100A	1.65V	175°C	D100E60	PG-TO247-3

Maximum Ratings

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V _{RRM}	600	V
Continuous forward current			
$T_{\rm C} = 25^{\circ}{\rm C}$		150	
$T_{\rm C} = 90^{\circ}{\rm C}$	/ _F	104	A
$T_{\rm C} = 100^{\circ}{\rm C}$		96	
Surge non repetitive forward current		400	^
$T_{\rm C} = 25^{\circ}{\rm C}, t_{\rm p} = 10$ ms, sine halfwave	I _{FSM}	400	A
Maximum repetitive forward current	1	300	А
$T_{\rm C} = 25^{\circ}{\rm C}, t_{\rm p}$ limited by $t_{\rm j,max}, D = 0.5$	I _{FRM}	300	A
Power dissipation			
$T_{\rm C} = 25^{\circ}{\rm C}$	D	375	14/
$T_{\rm C} = 90^{\circ}{\rm C}$	P _{tot}	212	W
$T_{\rm C} = 100^{\circ}{\rm C}$		198	
Operating junction temperature	Tj	-40+175	
Storage temperature	T _{stg}	-55+150	_∘c
Soldering temperature 1.6mm (0.063 in.) from case for 10 s	Ts	260	



Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic	· · ·			
Thermal resistance,	R _{thJC}		0.40	K/W
junction – case				
Thermal resistance,	R _{thJA}		40	
junction - ambient				

Electrical Characteristic, at T_j = 25 °C, unless otherwise specified

Parameter Symbol Conditions	Symbol	Conditions	Value			Unit
	Conditions	min.	typ.	max.	Unit	

Static Characteristic

Collector-emitter breakdown voltage	V _{RRM}	I _R =0.25mA	600	-	-	V
Diode forward voltage	V _F	<i>I</i> _F =100A				
		<i>T</i> _j =25°C	-	1.65	2.0	
		<i>T</i> _j =175°C	-	1.65	-	
Reverse leakage current	I _R	V _R =600V				μA
		$T_j=25^{\circ}C$	-	-	40	
		<i>T</i> _j =175°C	-	-	3300	

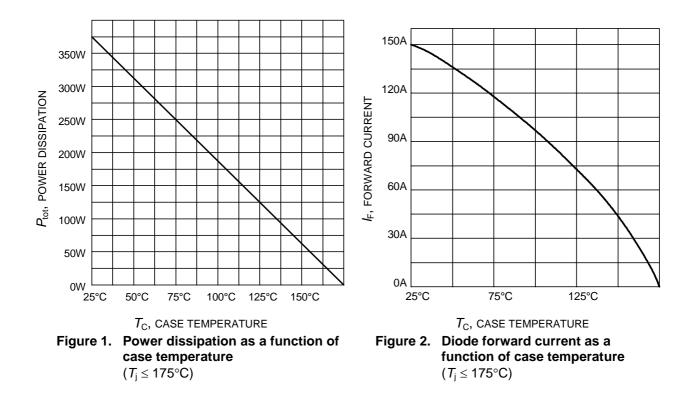
Dynamic Electrical Characteristics

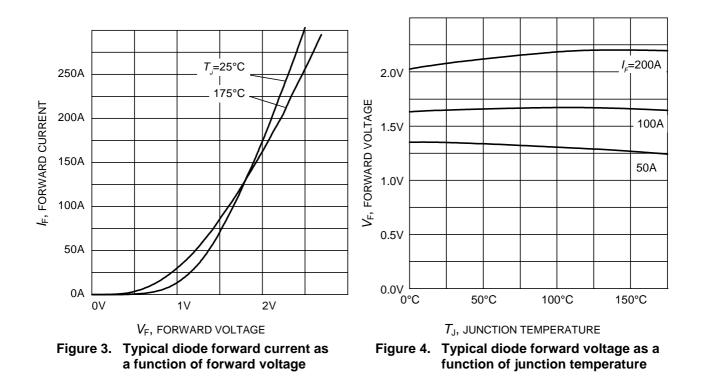
Diode reverse recovery time	t _{rr}	<i>T</i> _j =25°C	-	120	-	ns
Diode reverse recovery charge	Q _{rr}	$V_{\rm R} = 400 \rm V$,	-	3.6	-	μC
Diode peak reverse recovery current	I _{rr}	<i>I</i> _F =100A,	-	49.5	-	А
Diode peak rate of fall of reverse recovery current during $t_{\rm b}$	dI _{rr} /dt	dI _F /dt=1200A/µs	-	750	-	A/µs

Diode reverse recovery time	t _{rr}	<i>T</i> _j =125°C	-	168	-	ns
Diode reverse recovery charge	Q _{rrm}	$V_{\rm R} = 400 \rm V$,	-	5.8	-	μC
Diode peak reverse recovery current	I _{rr}	<i>I</i> _F =100A,	-	61.6	-	А
Diode peak rate of fall of reverse recovery current during $t_{\rm b}$	dI _{rr} /dt	dI _F /dt=1200A/µs	-	705	-	A/µs

Diode reverse recovery time	t _{rr}	<i>T</i> _j =175°C	-	200	-	ns
Diode reverse recovery charge	Q _{rrm}	V _R =400V,	-	7.8	-	μC
Diode peak reverse recovery current	I _{rr}	I _F =100A,	-	67.0	-	А
Diode peak rate of fall of reverse recovery current during $t_{\rm b}$	dI _{rr} /dt	<i>dI_F/dt</i> =1200A/µs	-	650	-	A/µs

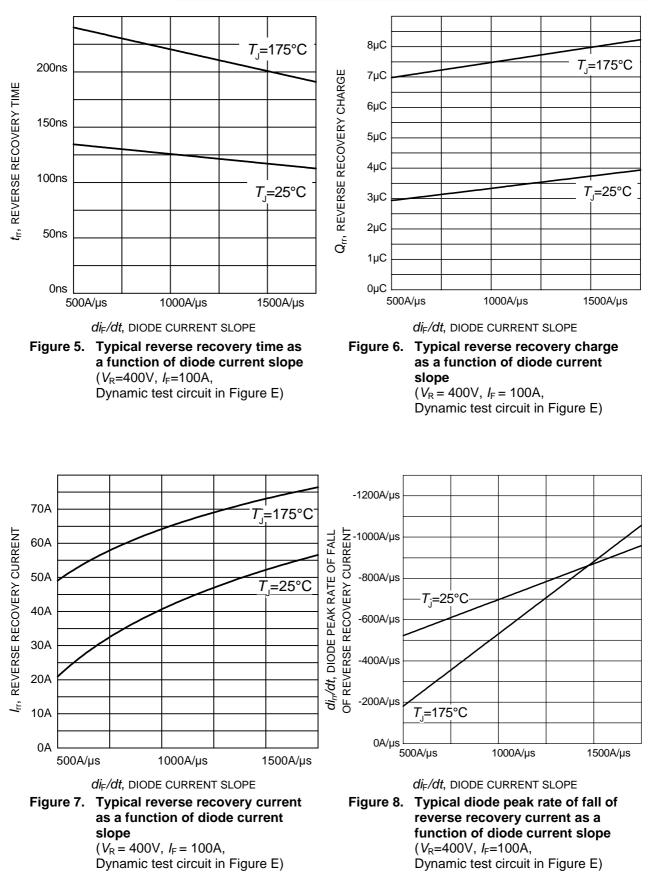






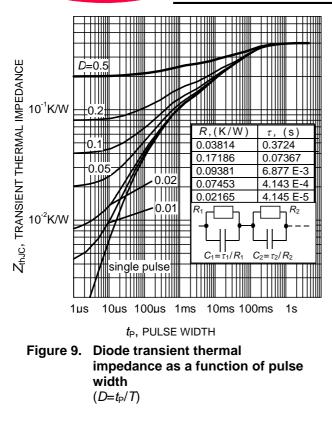
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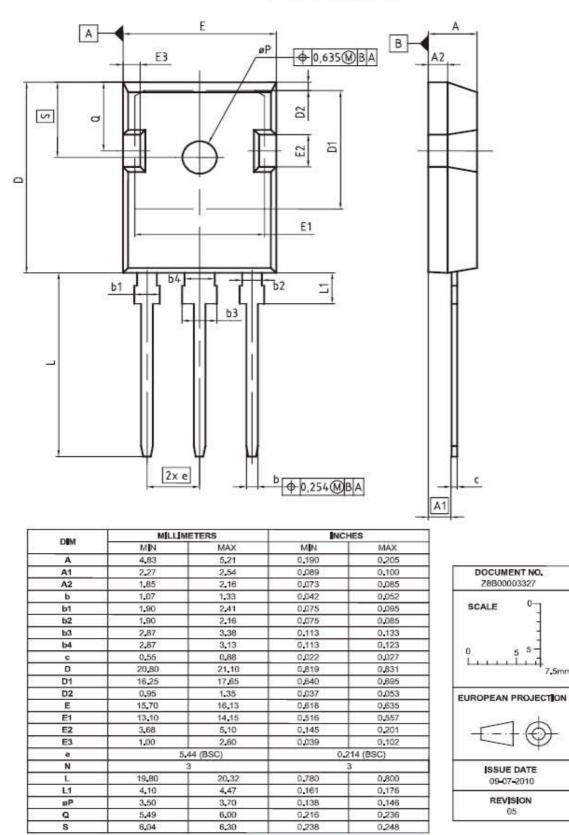




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PG-TO247-3



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